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SUPPLEMENTAL INFORMATION	:	Applicant: Berger
DISCLOSURE STATEMENT	:	Group Art Unit: 2811
BY APPLICANTS	:	Examiner: Nadav

OTHER DOCUMENTS

SWL 1. Amlani, I. et al., Digital Logic Gate Using Quantum-Dot Cellular Automata, *Science*, 284, pp. 289-291 (April 9, 1999).

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**U.S. PATENT DOCUMENTS**

Examiner's Initial	Document Number	Date	Name	Class/Sub-class
	NONE			

**FOREIGN PATENT DOCUMENTS**

Examiner's Initial	Document Number	Date	Country/Name	Translation yes/no
	NONE			

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